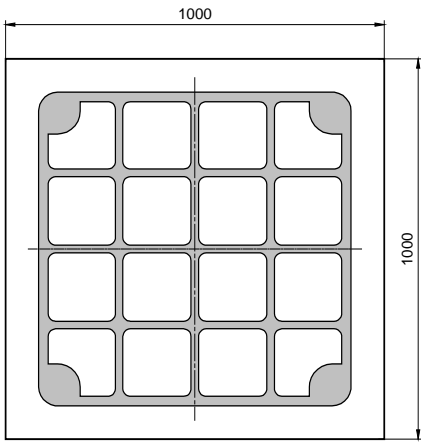


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up

 <p>PoC-05</p>	typ. dimensions (μm)	
	<u>typ. thickness</u> 160 (± 20) μm	
	<u>anode</u> gold alloy, 1.5 μm	
	<u>cathode</u> gold alloy, 0.5 μm dotted, 25% covered	

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.5	V
Forward voltage ²	$I_F = 350 \text{ mA}$	V_F		1.7	1.9	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power ¹	$I_F = 20 \text{ mA}$	Φ_e	3	4		mW
Radiant power ²	$I_F = 350 \text{ mA}$	Φ_e		62		mW
Radiant power ³	$I_F = 350 \text{ mA}$	Φ_e		120		mW
Radiant power ²	$I_F = 700 \text{ mA}$	Φ_e		200		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	860	870	880	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		45		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		10/25		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on bare chip glued on a $\varnothing 8 \times 1 \text{ mm}$ Cu header (10 s after switched on)

³Measured on epoxy covered chip glued on a $\varnothing 8 \times 1 \text{ mm}$ Cu header (10 s after switched on) with *EPIGAP* equipment (for information only)

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-870-11				

Packing: Chips on adhesive film with wire-bond side on top